

PRELIMINARY AMENDMENT
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In the Specification:

Please amend the seventh paragraph beginning on page 3 as follows:

[0016] The present invention is a substrate heater assembly of a substrate support for supporting a substrate in a process chamber (e.g., chemical vapor deposition (CVD) chamber, plasma enhanced CVD (PECVD) chamber, and the like) of a substrate processing system. The inventive substrate heater assembly may be used to facilitate deposition of material layers requiring low thickness non-uniformity ~~within~~ across a substrate (e.g., silicon (Si) wafer, and the like), as well within a batch of the substrates being processed. Herein either a CVD or PECVD chamber (or reactor) is referred to as a CVD chamber (or reactor).

Please amend the third paragraph beginning on page 4 as follows:

[0019] The reactor 100 comprises a process chamber 102 and a controller 110. The process chamber 102 generally comprises a body (wall) 130 having a lid assembly 118, a substrate support pedestal 126, a vacuum pump 104, and shield(s) 114 used to protect an inner surface of the wall 130 during a CVD process. The wall 130 is formed from a conductive material (e.g., aluminum (Al), stainless steel, and the like) and coupled to a ground terminal 176 of the process chamber 102.

Please amend the second paragraph beginning on page 5 as follows:

[0023] The temperature of the substrate 112 is controlled by stabilizing a temperature of the heater member 132. In one embodiment, the helium gas from a gas source 136 is provided via a gas conduit 166 to grooves (or, alternatively, positive dimples) 230 (shown using broken lines in FIG. 2 2A below) formed in the heater member 132 under the substrate 112. The helium gas provides a heat transfer between the heater member 132 and the substrate 112 and facilitates uniform heating of the substrate. Using such thermal control, the substrate 112 may be maintained at a temperature between about 200 and 800 degrees Celsius.

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Please amend the sixth paragraph beginning on page 5 as follows:

[0016] The lift pin mechanism 156 is used to lower the substrate 112 into the substrate pocket 150 of the substrate heater assembly 148 or to raise the substrate off the substrate heater assembly. The heater member 132 comprises a plurality of openings 232 (shown in FIG. 2 2A below) for lift pins of the mechanism 156.

Please amend the third paragraph beginning on page 10 as follows:

[0044] Thus, a heater assembly has been provided that promotes deposition uniformity while limiting deposition along the substrate's edge. In one embodiment, the advantageous features of the invention may be incorporated into the body of the heater assembly, thereby reducing the number of components and cost of the heater assembly while promoting chamber to chamber processing uniformity.